## **EAST Search History**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14261	etch\$3 near3 (sacrificial dielectric) and (gate with (sacrificial dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/09 13:46
12	36796	((substrate or wafer) with (dielectric or oxide or insulat \$3 or ILD IMD) with (gate polysilicon electrode) with (sacrificial dielectric or oxide or insulat \$3 or ILD IMD)) and (remov\$3 etch \$3) near1 (sacrificial dielectric or oxide or insulat \$3 or ILD IMD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/09
L3	7039	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/09 13:47

10/9/2008 1:47:16 PM

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